

L1085-35M00

Stem type LED

L1085-35M00 is an InGaAsP LED mounted on a TO-18 stem with an epoxy lens.

It is designed for high output power and wide viewing angle use.

On forward bias, it emits a spectral band of radiation, which peaks at 1085nm.

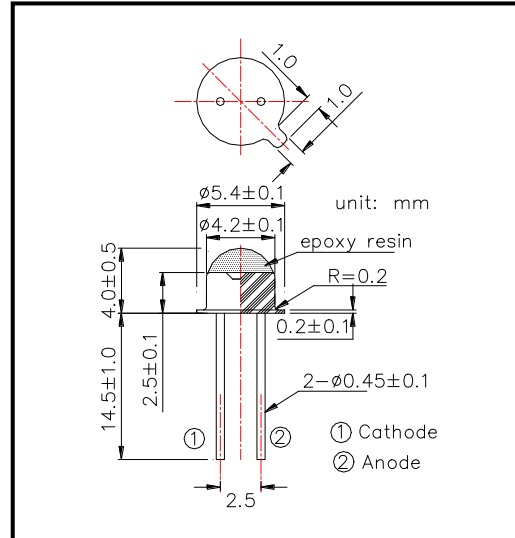
◆ Features

- 1) High radiated intensity
- 2) Wide Viewing angle

◆ Specifications

- 1) Product Name NIR stem type LED
- 2) Type No. L1085-35M00
- 3) Chip Spec.
 - (1) Material InGaAs/InP
 - (2) Peak Wavelength 1085nm
- 4) Package
 - (1) Type TO-18 stem
 - (2) Lens Epoxy resin

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _d	130	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	3	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.15	1.35	V
Reverse Current	I _R	V _R =5V			10	uA
Radiated Power	P _o	I _F =50mA	4.0	8.0		mW
Radiant Intensity	I _E	I _F =50mA		4.0		mW/sr
Peak Wavelength	λ _P	I _F =50mA	1060	1085	1100	nm
Half Width	Δλ	I _F =50mA		50		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		±45		deg.
Rise Time	t _r	I _F =50mA		30		ns
Fall Time	t _f	I _F =50mA		20		ns

‡Radiated Power is measured by HPK G8370-85.

‡Radiant Intensity is measured by Ando Optical Multi Meter AQ2140 & AQ2742